

Effects of High Temperature Pulsed Helium Implantation on Tungsten Surface Morphology

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Determine the effect of helium and deuterium implantation on the surface morphology of tungsten at high temperatures for High Averaged Power Laser (HAPL) project

- Why: To evaluate whether tungsten will serve as a suitable material for ICF first wall application
- How: Use IEC device to irradiate materials with He⁺ and D⁺ ions. Then use Scanning Electron Microscopy and Focused Ion Beam to determine morphology changes



IEC Cathode was Replaced with W Sample for Implantation Studies





Deuterium Implantation Caused Substantial Grain Growth



As Received

2x10¹⁹ D⁺/cm², 20-40 kV 1000-1300 °C









New Design Allows Pulsed IEC Operation



- Currently able to pulse up to 115 kV
- Operation has been performed with pulses as short as 100 μs
- Capable of running D₂ and/or He fuel gas









Pulsed Irradiation Caused Increased Damage to Tungsten Surface at 6x10¹⁸ He⁺/cm²







Pulsed Irradiation Created Coral-Like Tungsten Features at 10¹⁹ He⁺/cm²



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2 hour runtime

30 kV, 6 mA Steady-State (1150<u>+</u>20 °C) 30 minute runtime

Mass Loss was Measured for Pulsed Tungsten Samples

- There has been no observable mass loss at fluences below 10¹⁹/cm² for steady-state irradiation at 1150 °C
- Measured mass loss and corresponding thickness loss for pulsed irradiation is shown below:

| Helium Fluence | 1x10 ¹⁹ | 6x10 ¹⁸ | 1x10 ¹⁸ |
|------------------------|----------------------|-----------------------|-----------------------|
| Mass Loss (2 g sample) | 4.2 <u>+</u> 0.1 mg | 3.6 <u>+</u> 0.1 mg | 0.5 <u>+</u> 0.1 mg |
| Thickness Loss | 1.1 <u>+</u> 0.03 μm | 0.93 <u>+</u> 0.03 μm | 0.13 <u>+</u> 0.03 μm |

1 ms pulse width, 25 Hz, 1150 °C

- Reference HAPL W armor could lose 50 µm/FPY (~1200 kg/FPY) due to low energy He irradiation alone
- Losses as high as 200 mm/FPY are predicted for full He spectra

Implications

- In ICF first walls and MFE divertors, the high density of small pores could act as:
 - Nucleation sites for cracks under repeated shock loading
 - Sites for initiating the formation of "dust"
 - Release sites for implanted He
- In IEC cathodes:
 - Embedded helium contributing to the D-³He rate appears to saturate around 10¹⁸ He/cm²
 - Sharp points created by pore formation may cause high voltage breakdown

Conclusions

- Switching from steady-state to pulsed irradiation at 1150 °C resulted in an increased surface roughening over 10¹⁸ to 10¹⁹ He⁺/cm² range
- Porous layer in tungsten was ~3x thicker after pulsed irradiation compared to steady-state
- Mass loss of tungsten armor in Reference HAPL design could be as much as 50 μ m/FPY (~1200 kg/FPY), which is well beyond calculated physical sputtering values

Questions?

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